

Improvement of dielectric loss tangent of doped $\text{Ba}_{0.5}\text{Sr}_{0.5}\text{TiO}_3$ thin films for tunable microwave devices

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Al_2O_3 doped $\text{Ba}_{0.5}\text{Sr}_{0.5}\text{TiO}_3$ (BST) thin films, with different Al_2O_3 contents, were deposited on (100) LaAlO_3 substrate, by pulsed laser deposition (PLD) technique to develop agile thin films for tunable microwave device applications. The dielectric properties of Al_2O_3 doped BST films were determined with non-destructive dual resonator near 7.7 GHz. The effects of Al_2O_3 doping are the significant reduction of dielectric constant, dielectric loss and tunability, compared with pure BST thin film. The figure of merit for Al_2O_3 doped BST films have also been shown to increase with Al_2O_3 content. Consequently, Al_2O_3 doped BST films have the potential to be exploited in tunable microwave device applications.

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I. INTRODUCTION

It is a challenging task for microwave communication researchers to develop tunable microwave devices. One of the approaches is to use a ferroelectric thin film as a buffer layer, while the dielectric constant ϵ_r of the ferroelectric thin film can be tuned by applying an electric field and hence the working frequency of the microwave devices can be tuned accordingly^{1,2,3,4}. The forerunner candidate of a hybrid multi-layer thin film system involves $\text{Ba}_{1-x}\text{Sr}_x\text{TiO}_3$ (BST) where x is the concentration of the constituent which can be tuned as well. An additional advantage of BST is the Curie temperature (T_c) of BST dependence on x . Therefore, the working temperature of the tunable microwave devices can be tuned as well^{5,6,7,8}. Unfortunately, the dielectric loss $\tan \delta$ of the BST is normally high, which is around 0.03 for $x = 0.5$ in the present study on pulsed laser deposited thin film. The reported values of $\tan \delta$ for BST from different research groups are varied. In general, the values of $\tan \delta$ are too high for BST to be useful to be of practical use in microwave tunable devices. It is a general belief that $\tan \delta$ values have to be lower than 0.01 for BST thin films to be useful in the microwave devices^{9,10,11}. In the present study, we chose to address the problem of dielectric loss by doping the BST with low loss oxide^{12,13,14}. The Al_2O_3 is chosen for its low microwave dielectric loss as a dopant. The dielectric properties of doped ferroelectric film is measured by a home-made microstrip dual resonator near 7.7 GHz. The result was then checked by measuring the ϵ_r of LaAlO_3 single crystal substrate.

II. EXPERIMENTAL

BST target with diameter 2.5 cm was prepared using BaTiO_3 , SrTiO_3 powders with ratio 1:1, via the conventional ceramic processing. The BaTiO_3 and SrTiO_3 powders were mixed and calcined at 950 °C for 1 hour before they were compacted and sintered at 1350 °C for 4 hours. The Al_2O_3 doped BST thin films were deposited on (100) LaAlO_3 single crystal substrates with size of 10 × 5 × 0.5 mm³, by PLD with a KrF excimer laser at repetition rate of 5 Hz, and the average pulse energy was 250 mJ. BST target with Al_2O_3 plates on its surface was employed in the film deposition. The Al_2O_3 doped BST film deposition as carried out at substrate temperature of 650 °C and an oxygen pressure of 0.2 mbar for 45 minutes. The post-deposition annealing was done in the PLD chamber at the same temperature but with a higher oxygen pressure of 1.0 atm. The optimum distance between substrate and target was 4.5 cm for this temperature and pressure. The content of Al_2O_3 in the deposited Al_2O_3 doped BST films are controlled by coverage area of Al_2O_3 over the BST target. BST film without doping was also deposited for comparison. The films produced from the targets with 10 percents, 20 percents, 30 percents and 40 percents Al_2O_3 coverage of the BST target were abbreviated to BSTA1, BSTA2, BSTA3 and BSTA4. The Al_2O_3 content in the films were characterized by Rutherford Backscattering Analysis (RBS), and the relative concentration of Al_2O_3 in BSTA1: BSTA2: BSTA3: BSTA4 were found to be 1 : 4 : 6 : 9. Structural phase composition and crystallization of the Al_2O_3 doped BST thin films were determined by X-ray diffraction (XRD), using a Philips PW 1729 type X-ray

TABLE I: Dielectric properties of the Al_2O_3 doped BST thin films at microwave frequency 7.7 GHz

Thin film	ϵ_r	$\tan \delta$ [for 0 bias]	Tunability [percentage]	
BST	1622	0.030	22.0	7.33
BSTA 1	1387	0.021	19.7	9.38
BSTA 2	1311	0.015	17.9	11.93
BSTA 3	950	0.0123	16.4	13.67
BSTA 4	870	0.011	15.9	14.45

di ractometer. Surface morphology was examined by scanning electron microscopy (SEM), using a JEOL JSM-6340F type field emission scanning electron microscope. The dielectric properties of Al_2O_3 doped BST thin films in terms of ϵ_r and $\tan \delta$ were measured by a home-made non-destructive microstrip dual-resonator method at room temperature and microwave frequency 7.7 GHz^{15,16}. The microstrip dual-resonator patterned on a TMM10i microwave substrate, consists of two planar half-wavelength resonators coupled through a gap of 36 μm . The film under test was placed on top of the microstrip circuit, covering the gap between two microstrip resonators. The ϵ_r and $\tan \delta$ of the films were derived from the resonant frequencies f_1 , f_2 and the corresponding quality factor Q_1 , Q_2 , of the microstrip dual-resonator. In the study of the electric field dependence of the Al_2O_3 doped BST thin films, a maximum dc voltage of 2.1 kV was applied through two electrode pads on the microstrip circuit board across a gap of about 2.6 mm, corresponding to a maximum electric field of 8.1 kV/cm.

III. RESULTS AND DISCUSSION

Fig. 1 shows the XRD patterns of the deposited thin films. It is found that all the films have a single phase perovskite structure. The intensity peak was broadened with increasing Al_2O_3 dopant, which means that the grain size of the Al_2O_3 doped BST thin films decreased as a result of increased Al_2O_3 content. The Al_2O_3 was not detected by XRD due to the relatively small amount of Al_2O_3 compared with BST. However, for the BSTA 4 film, two unidentified peaks were observed at $2\theta = 39.39^\circ$ and $2\theta = 43.01^\circ$ (marked \ast) as in Fig. 1). These peaks are attributed to a second phase caused by the excessive Al_2O_3 content. The second phase might be undesirable for the film to be applied in microwave devices. This would put a limit on the amount of dopant.

Fig. 2 displays the surface morphology of the Al_2O_3 doped BST thin films by SEM. The films exhibited a dense microstructure, which was greatly modified by Al_2O_3 doping. It is found that the surface roughness increases with the increase of Al_2O_3 content, and it is consistent with the XRD data. Furthermore, the thicknesses of the thin films were estimated as 500 nm in average from a cross-sectional SEM image.

The ϵ_r of the Al_2O_3 doped BST thin films as a function of applied electric field are shown in Fig. 3. The pure BST film has $\epsilon_r = 1622$ that is higher than doped films, BSTA 1 ($\epsilon_r = 1387$), BSTA 2 ($\epsilon_r = 1311$), BSTA 3 ($\epsilon_r = 950$) and BSTA 4 ($\epsilon_r = 870$). The ϵ_r of Al_2O_3 doped BST thin films decrease with increasing Al_2O_3 content. The high ϵ_r values are due to the fact that all thin films are epitaxially c-axis oriented, which are indicated by (100) and (200) peaks in XRD patterns. The highly c-axis oriented films provide a strong polarization direction compared to randomly oriented samples, and tends to form a concentrated polarization which results in higher ϵ_r . Fig. 4 depicts the plot for $\tan \delta$ of Al_2O_3 doped BST thin films as a function of the applied electric field. The $\tan \delta$ decreased as 0.030, 0.021, 0.015, 0.012 and 0.011, corresponding to the samples BST, BSTA 1, BSTA 2, BSTA 3 and BSTA 4, respectively.

It is known that tunable microwave device applications, require a high dielectric constant and low dielectric loss. The dielectric tunability was calculated by the formula,

$$\text{tunability} = \frac{\epsilon_{r0} - \epsilon_{rb}}{\epsilon_{r0}}; \quad (1)$$

where ϵ_{r0} and ϵ_{rb} represent the dielectric constant value at zero applied electric field and the maximum applied electric field, respectively. The dielectric properties of Al_2O_3 doped BST thin films were listed in Table 1. Identical to dielectric constant and loss tangent, the dielectric tunability also reduces as a consequence of Al_2O_3 doping. We found that the dielectric tunability was reduced from 22.0 percents (BST thin film) to 15.9 percents (BSTA 4). In tunable microwave devices application, figure of merit is usually used to compare the quality of ferroelectric films, which is defined as,

$$F = \frac{\text{tunability}}{\tan \delta}; \quad (2)$$

One can notice that F -factor is proportional to Al_2O_3 content, as given in Table 1 in which $F = 7.33$ (BST) and $F = 14.5$ (BSTA 4).

IV. SUMMARY

In conclusion, we demonstrated that highly c-axis oriented Al_2O_3 doped BST thin films could be deposited on (100) LaAlO_3 single-crystal substrate, by PLD technique. It is found that ϵ_r , $\tan \delta$ and dielectric tunability of the Al_2O_3 doped BST thin films have decreased due to increasing Al_2O_3 content. As a result of this, F -factor were improved significantly. The Al_2O_3 substitution into BST thin films is observed to significantly modify the microstructure of the films. Our results showed the dielectric properties of BST ferroelectric thin films can be readily modified to meet the requirements of microwave device applications with Al_2O_3 doping.

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- FIG. 1: XRD patterns of the Al_2O_3 doped BST films on LaAlO_3 substrates, (a) BSTA1, (b) BSTA2, (c) BSTA3 and (d) BSTA4.
- FIG. 2: Surface morphology of the Al_2O_3 doped BST films on LaAlO_3 substrates, (a) BSTA1, (b) BSTA2, (c) BSTA3 and (d) BSTA4
- FIG. 3: Dielectric constant of the Al_2O_3 doped BST films on LaAlO_3 substrates as a function of applied electric field.

FIG. 4: Loss tangent of the Al_2O_3 doped BST films on LaAlO_3 substrates as a function of applied electric field.